





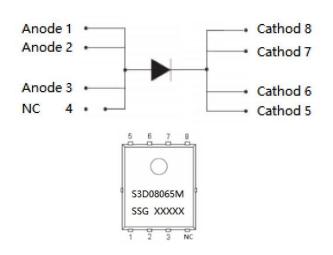
# S3D08065M 650V SIC POWER SCHOTTKY RECTIFIER



#### **Description**

S3D08065M is a SiC Schottky rectifier packaged in PDFNWB5×6-8L case. The device is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D08065M is ideal for energy sensitive, high frequency applications in challenging environments.

### **Circuit Diagram**



### **Features**

- 175°C T<sub>J</sub> operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- · High package isolation voltage
- Terminals finish: 100% Pure Tin
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

### **Applications**

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection







# **Maximum Ratings**

Characteristics	Symbol	mbol Condition		Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>DC</sub>	-	650	V
Average Rectified Forward Current	I <sub>F (AV)1</sub>	@Tc=25°C	24	А
, werage resumes remains canonic	I <sub>F (AV)2</sub>	@Tc=153°C	8	А
Repetitive Peak Forward Surge Current	I <sub>FRM1</sub>	10ms, Half Sine pulse, T <sub>C</sub> =25°C	37.5	А
	I <sub>FRM2</sub>	10ms, Half Sine pulse, T <sub>C</sub> =110°C	25.5	Α
Book One Cycle New Bonetitive Come Coment	I <sub>FSM1</sub>	10ms, Half Sine pulse, T <sub>C</sub> =25°C	71	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM2</sub>	10ms, Half Sine pulse, T <sub>C</sub> =110°C	60	Α
Non-Repetitive Peak Forward Surge Current	I <sub>F,Max1</sub>	10µs. Pulse, T <sub>C</sub> =25℃	650	А
Non-repetitive reak rorward ourge ourrent	I <sub>F,Max2</sub>	10µs. Pulse, T <sub>C</sub> =110°C	530	А
Dower Discinction	P <sub>tot1</sub>	T <sub>J</sub> =25°C	79.0	W
Power Dissipation	P <sub>tot2</sub>	T <sub>J</sub> =110°C	34.2	W

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub> @ 8A, Pulse, T <sub>J</sub> = 25 °C		1.4	1.7	V
	V <sub>F2</sub>	@ 8A, Pulse, T <sub>J</sub> = 175 °C	1.7	2.4	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}\text{C}$	3	20	uA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 175  ^{\circ}\text{C}$	30	200	uA
Junction Capacitance	Ст	VR=0V, Tj=25℃,f=1MHz	650	-	pF
Reverse Recovery Charge	Qc	I <sub>F</sub> = 8A, di/dt = 500A/μs VR = 400 V, T <sub>J</sub> =25°C	40.55	-	nC
Capacitance Stored Energy	Ec	V <sub>R</sub> = 400 V	9.93	-	μЈ

<sup>\*</sup> Pulse width < 300  $\mu$ s, duty cycle < 2%

## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R <sub>0</sub> JC	DC operation	1.9	°C/W

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## **Marking Diagram**



Where XXXXX is YYWWL

 S3D
 = Device Type

 M
 = Package type

 08
 = Forward Current (8A)

 065
 = Reverse Voltage (650V)

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

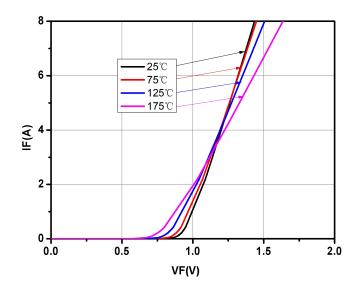
Epoxy resin UL:94V-0

# **Ordering Information**

Device	Package	Shipping
S3D08065M	PDFNWB5×6-8L	3000pcs/Reel
S3D08065MTR	PDFNWB5×6-8L	3000pcs/Reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Ratings and Characteristics Curves**



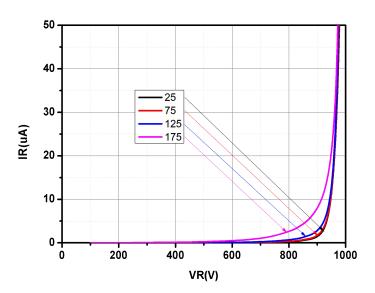


Fig.1-Typical Forward Voltage Characteristics

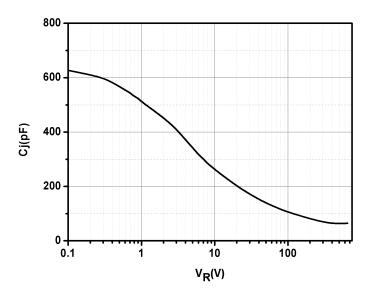
Fig.2-Typical Reverse Characteristics

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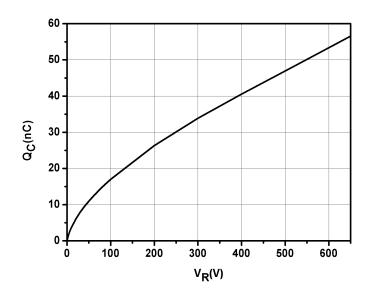
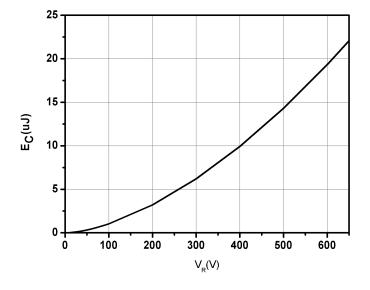


Fig.3-Capacitance vs. Reverse Voltage

Fig.4-Total Capacitance Charge vs. Reverse Voltage



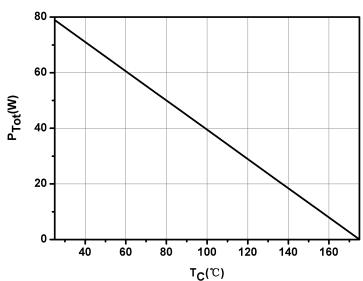


Fig.5-Capacitance Stored Energy

Fig.6-Power Derating

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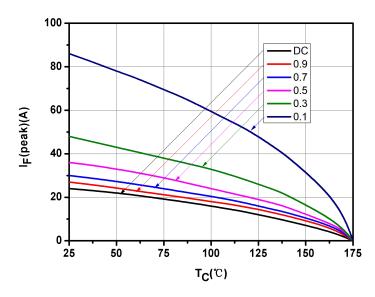
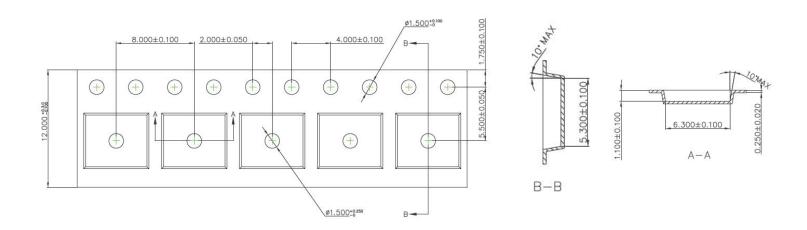


Fig.7-Current Derating

# Carrier Tape & Reel Specification PDFNWB5×6-8L



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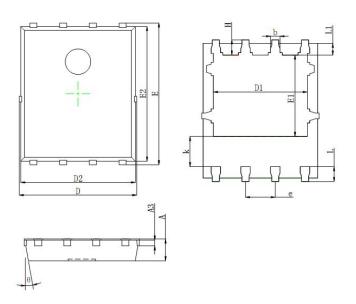
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#### **Mechanical Dimensions PDFNWB5**×6-8L



SYMBOL	Millin	neters	Inches		
STWIDOL	Min.	Max.	Min.	Max.	
Α	0.900	1.000	0.035	0.039	
A3	0.254	REF.	0.010REF.		
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
е	1.270	TYP.	0.050 TYP.		
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
Θ	10°	12°	10°	12°	

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